Electronic structure and magnetic properties of Dy-doped ${\rm Bi}_{2}{\rm Te}_{3}$

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Doping the topological insulator Bi_2Te_3 with rare-earth ions is a way to introduce the high magnetic moments into the material [1]. Ferromagnetic order can break timereversal symmetry, opening a gap in the topological surface states. The correlated band theory implemented as a combination of the relativistic density functional theory with the Anderson impurity model [2] is applied to theoretical investigation of the electronic and magnetic character, and the magnetic anisotropy for Dy-doped Bi₂Te₃ topological insulator. For both ferro- and anti-ferromagnetic Dy-planes in Bi₂Te₃ we found the in-gap flat *f*-bands located at the top of the valence band of Bi₂Te₃. The positive uniaxial MAE is predicted for $(\text{Dy}_x\text{Bi}_{1-x})_2\text{Te}_3$ with x = 0.33. The experimental resonant photoemission spectra are well reproduced by the calculations [3]. These studies can be important to explore the potential use of rare-earth doped topological insulators in the low-power spintronic devises.

References:

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